



## QL63H5S-A/B/C InGaAlP Laser Diode

*Tentative*

Ver. 3 2006

### ◆ OVERVIEW

QL63H5S-A/B/C is a MOCVD grown 635nm band *InGaAlP* laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 20mW for optoelectronic devices such as Optical Leveler and Modules.

### ◆ APPLICATION

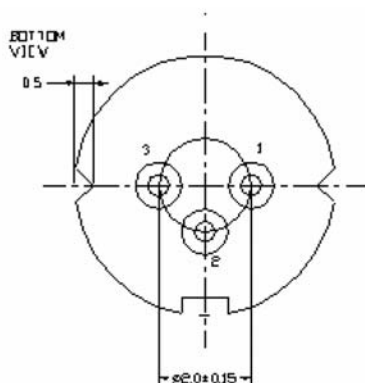
- Bar Code Scanner
- Laser Module

### ◆ FEATURES

- Visible Light Output :  $\lambda_p = 635 \text{ nm}$
- Optical Power Output : 20mW CW
- Package Type : TO-18 (5.6mm $\phi$ )
- Built-in Photo Diode for Monitoring Laser Diode

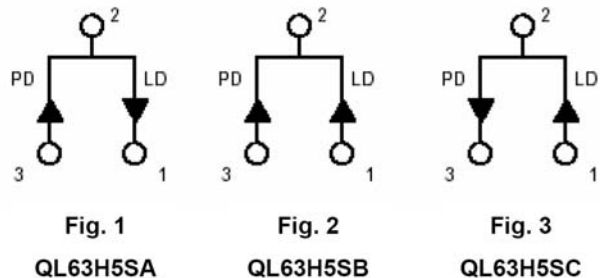
### ◆ ELECTRICAL CONNECTION

#### Bottom View



#### Pin Configuration

A	LD cathode, PD anode (Fig. 1)
B	LD, PD anode (Fig. 2)
C	LD anode, PD cathode (Fig. 3)





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### ◆ ABSOLUTE MAXIMUM RATING at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	P	24	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	-10 ~ +50	°C
Storage Temperature	Tstg	-40 ~ +85	°C

### ◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C <sup>1)2)</sup>

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	20	-	mW	-
Threshold Current	Ith	-	30	50	mA	Po=20mW
Operating Current	Iop	-	60	80	mA	Po=20mW
Operating Voltage	Vop	-	2.3	2.6	V	Po=20mW
Lasing Wavelength	λp	630	639	645	nm	Po=20mW
Beam Divergence <sup>3)</sup>	θ	6	8	11	deg	Po=20mW
	θ ⊥	25	30	35	deg	Po=20mW
Beam Angle	Δθ	-	-	±2.0	deg	Po=20mW
	Δθ ⊥	-	-	±3.0	deg	Po=20mW
Monitor Current	Im	0.05	0.25	0.7	mA	Po=20mW
Optical Distance	ΔX, ΔY, ΔZ	-	-	±60	μm	-

1) Initial values      2) All above values are evaluated with measuring apparatus

3) Full angle at half maximum

**NOTICE : QL63H5S-A/B/C to be operated on APC**  
**The above product specifications are subject to change without notice.**



## ◆ PACKAGE DIMENSION

